

Data Sheet Issue:- 3

Rectifier Diode Types W1185LC300 to W1185LC450 Previous Type No.: SW38-45CXC515

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{RRM}	Repetitive peak reverse voltage, (note 1)	3000-4500	V
V _{RSM}	Non-repetitive peak reverse voltage, (note 1)	3100-4600	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I _{F(AV)M}	Maximum average forward current, T _{sink} =55°C, (note 2)	1185	А
I _{F(AV)M}	Maximum average forward current. T _{sink} =100°C, (note 2)	833	А
I _{F(RMS)M}	Nominal RMS forward current, T _{sink} =25°C, (note 2)	2171	А
I _{F(d.c.)}	D.C. forward current, T _{sink} =25°C, (note 3)	1936	А
I _{FSM}	Peak non-repetitive surge t_p =10ms, V_m =60% V_{RRM} , (note 4)	9.2	kA
I _{FSM2}	Peak non-repetitive surge t _p =10ms, V _m ≤10V, (note 4)	10.58	kA
l ² t	$I^{2}t$ capacity for fusing t _p =10ms, V _{rm} =60%V _{RRM} , (note 4)	0.423×10 ⁶	A ² s
l ² t	$I^{2}t$ capacity for fusing t _p =10ms, V _{rm} ≤10V, (note 4)	0.559×10 ⁶	A ² s
T _{j op}	Operating temperature range	-55 to +160	°C
T _{stg}	Storage temperature range	-55 to +185	°C

Notes:-

1) De-rating factor of 0.13% per °C is applicable for T_j below 25°C.

2) Double side cooled, single phase; 50Hz, 180° half-sinewave.

3) Double side cooled.

4) Half-sinewave, $160^{\circ}C T_{j}$ initial.



Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{FM}	Maximum peak forward voltage	-	-	2.4	I _{FM} =2420A	V
V _{T0}	Threshold voltage	-	-	1.00		V
r _T	Slope resistance	-	-	0.575		mΩ
I _{RRM}	Peak reverse current	-	-	30	Rated V _{RRM}	mA
Б	Thermal registeries, junction to bestaink	-	-	0.033	Double side cooled	K/W
R _{thJK}	Thermal resistance, junction to heatsink	-	-	0.065	Single side cooled	K/W
F	Mounting force	10	-	20	Note 2	kN
W _t	Weight		340			g

Notes:-

1) Unless otherwise indicated $T_j=160^{\circ}C$.

2) For other clamp forces, please consult factory.



Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	V _{RRM} V	V _{RSM} V	V _R DC V
30	3000	3100	1750
38	3800	3900	1950
45	4500	4600	2120

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T_i below 25°C.

4.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

and:

 $W_{AV} = rac{\Delta T}{R_{th}}$

 $\Delta T = T_{i\max} - T_K$

5.0 Computer Modelling Parameters

5.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_{T0} + \sqrt{V_{T0}^{2} + 4 \cdot ff^{2} \cdot r_{T} \cdot W_{AV}}}{2 \cdot ff^{2} \cdot r_{T}}$$

Where V_{T0} =1.00V, r_T=0.575m Ω ,

 R_{th} = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

Supplementary Thermal Impedance						
Conduction Angle	6 phase (60°)	3 phase (120°)	1/2 wave (180°)	d.c.		
Square wave Double Side Cooled	0.0455	0.0393	0.0362	0.0319		
Square wave Cathode Side Cooled	0.0753	0.0711	0.0687	0.0646		
Sine wave Double Side Cooled	0.0397	0.0350	0.0313			
Sine wave Cathode Side Cooled	0.0699	0.0677	0.0653			

Form Factors						
Conduction Angle6 phase (60°)3 phase (120°)½ wave (180°)d.c.						
Square wave	2.449	1.732	1.414	1		
Sine wave	2.778	1.879	1.57			



5.2 Calculating V_F using ABCD Coefficients

The on-state characteristic I_F vs. V_F , on page 8 is represented in two ways;

- (i) the well established V_{T0} and r_T tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V_F in terms of I_F given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V_F agree with the true device characteristic over a current range, which is limited to that plotted.

160°C Coefficients						
Α	0.5748073					
В	0.04333389					
С	0.4645497×10 ⁻³					
D	7.867421×10 ⁻³					



5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}}\right)$$

Where p = 1 to *n*, *n* is the number of terms in the series and:

- t = Duration of heating pulse in seconds.
- $r_t =$ Thermal resistance at time t.
- r_p = Amplitude of p_{th} term.
- τ_p = Time Constant of r_{th} term.

The coefficients for this device are shown in the tables below:

D.C. Double Side Cooled							
Term	Term 1 2 3 4						
r _ρ	0.017719	4.2406×10 ⁻³	6.9638×10 ⁻³	3.04366×10 ⁻³			
τρ	0.708578	0.1435833	0.036152	2.1308×10 ⁻³			

	D.C. Single Side Cooled							
Term	Term 1 2 3 4 5							
r _p	0.04013	6.3388×10 ⁻³	0.011408	6.0275×10 ⁻³	7.2098×10 ⁻⁴			
τρ	4.07311	2.15774	0.19931	9.0689×10 ⁻³	4.66345×10 ⁻⁴			

6.0 Reverse recovery ratings

(i) Q_{ra} is based on 50% I_{rm} chord as shown in Fig. 1



Fig. 1

(ii) Q_{rr} is based on a 150µs integration time i.e.

$$Q_{rr} = \int_{0}^{150\,\mu s} i_{rr}.dt$$

(iii)

K Factor =
$$\frac{t_1}{t_2}$$



Curves



Figure 1 – Mean forward current vs. power dissipation- Double side cooled









Figure 3 – Max. heatsink temperature vs. mean forward current – Double side cooled





Mean forward current (A) (Whole cycle averaged)





Figure 5 – Forward characteristics of limit device

Maximum instantaneous forward voltage (V)













Outline Drawing & Ordering Information

